

General Description:

The LWS1H08H8 uses advanced SGT technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is TO-220AB, which accords with the ROHS standard and Halogen Free standard.

Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- Battery switching application
- Hard switched and high frequency circuits
- Power Management

100% DVDS Tested

100% Avalanche Tested



Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
S1H08/LW H8/D.C.	LWS1H08H8	TO-220AB	Tube	50 Pcs

Absolute Maximum Ratings:

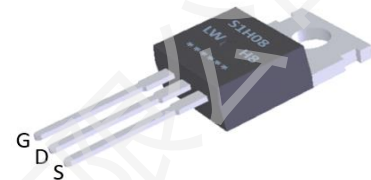
Symbol	Parameter		Value	Units
V_{DSS}	Drain-to-Source Voltage		-100	V
I_D	Continuous Drain Current	$T_C=25^{\circ}\text{C}$	-135	A
	Continuous Drain Current	$T_C=100^{\circ}\text{C}$	-85	A
I_{DM}^{a1}	Pulsed Drain Current		-540	A
E_{AS}^{a2}	Single pulse avalanche energy		1232	mJ
V_{GS}	Gate-to-Source Voltage		± 20	V
P_D	Power Dissipation		305	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		150, -55 to 150	$^{\circ}\text{C}$
T_L	Maximum Temperature for Soldering		260	$^{\circ}\text{C}$

Thermal Characteristics:

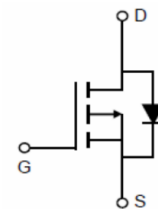
Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.4	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}^{a3}$	Thermal Resistance, Junction-to-Ambient	62	$^{\circ}\text{C}/\text{W}$

V_{DSS}	-100	V
I_D	-135	A
P_D	305	W
$R_{DS(ON) \text{ TYPE}}$	7.0	$\text{m}\Omega$

Marking and Pin Assignment



Inner Equivalent Principium Chart



Electrical Characteristic ($T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-100	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=-100V, V_{GS}=0V$	--	--	-1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=-20V, V_{DS}=0V$	--	--	-100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=+20V, V_{DS}=0V$	--	--	100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-2.0	-3.0	-4.0	V
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=-10V, I_D=-20A$	--	7.0	9.0	$m\Omega$

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS}=0V$	--	11687	--	pF
C_{oss}	Output Capacitance	$V_{DS}=-50V$	--	998	--	
C_{rss}	Reverse Transfer Capacitance	$f=1.0MHz$	--	139	--	
R_G	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	--	1.7	--	Ω

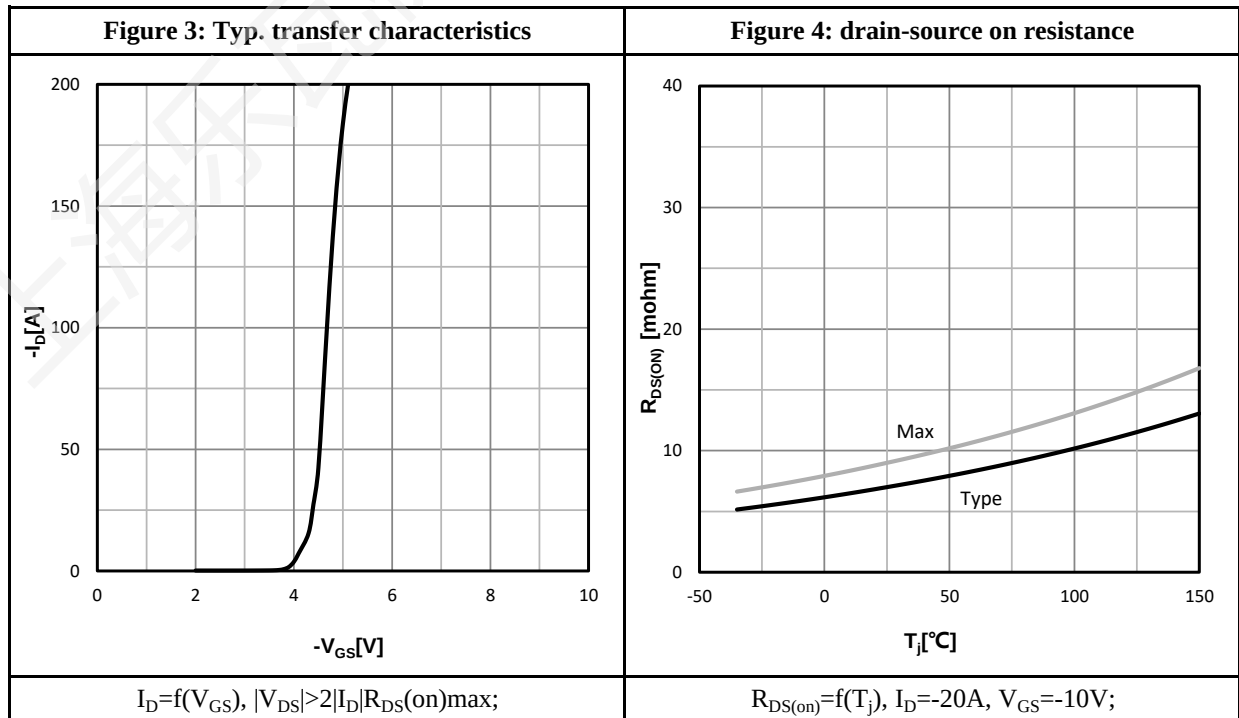
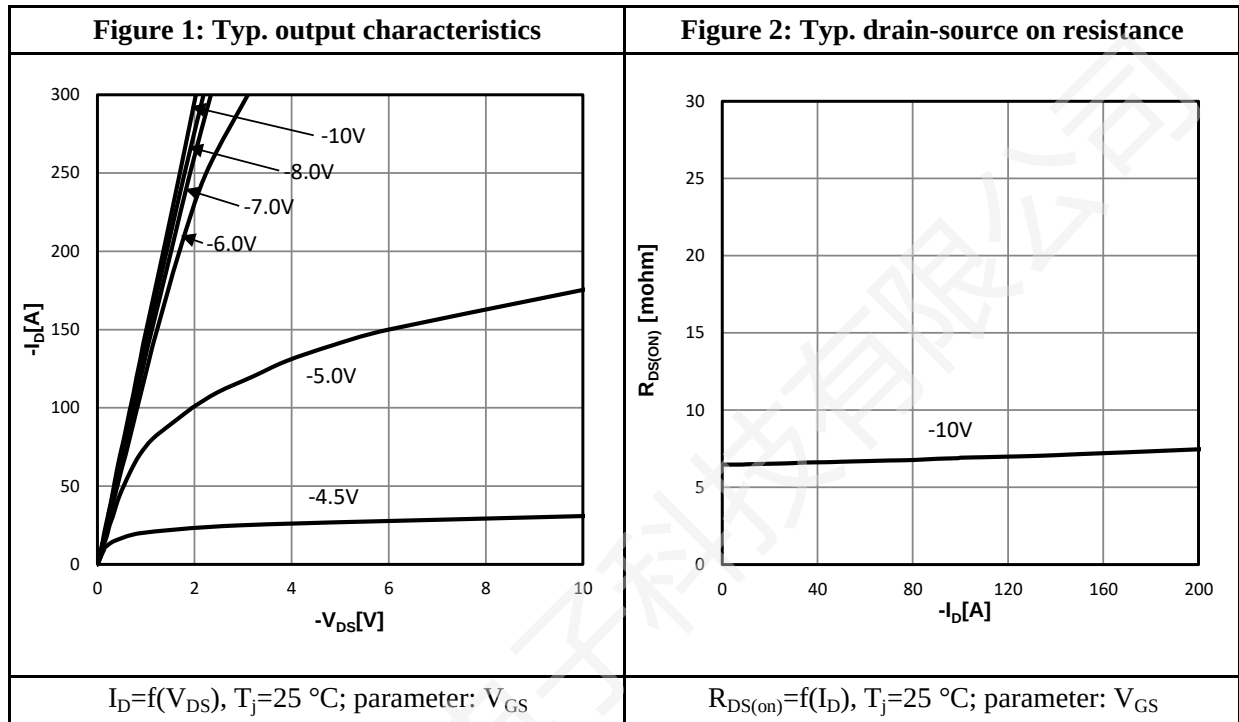
Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=-20A$	--	15	--	ns
t_r	Rise Time	$V_{DS}=-50V$	--	35	--	
$t_{d(OFF)}$	Turn-Off Delay Time	$V_{GS}=-10V$	--	100	--	
t_f	Fall Time	$R_G=1.0\Omega$	--	35	--	
Q_g	Total Gate Charge	$V_{GS}=-10V$	--	170	--	nC
Q_{gs}	Gate to Source Charge	$V_{DS}=-50V$	--	45	--	
Q_{gd}	Gate to Drain Charge	$I_D=-20A$	--	31	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	$T_C=25\text{ }^{\circ}\text{C}$	--	--	-135	A
V_{SD}	Diode Forward Voltage	$I_S=-20A, V_{GS}=0V$	--	--	-1.2	V
t_{rr}	Reverse Recovery Time	$I_S=-20A, V_{DD}=-50V$	--	86	--	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt=100A/\mu s$	--	271	--	nC

a1: Repetitive rating; pulse width limited by maximum junction temperature

a2: $V_{DD}=-70V, L=0.1mH, R_G=25\Omega$, Starting $T_j=25\text{ }^{\circ}\text{C}$

a3: Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection.

Characteristics Curve:


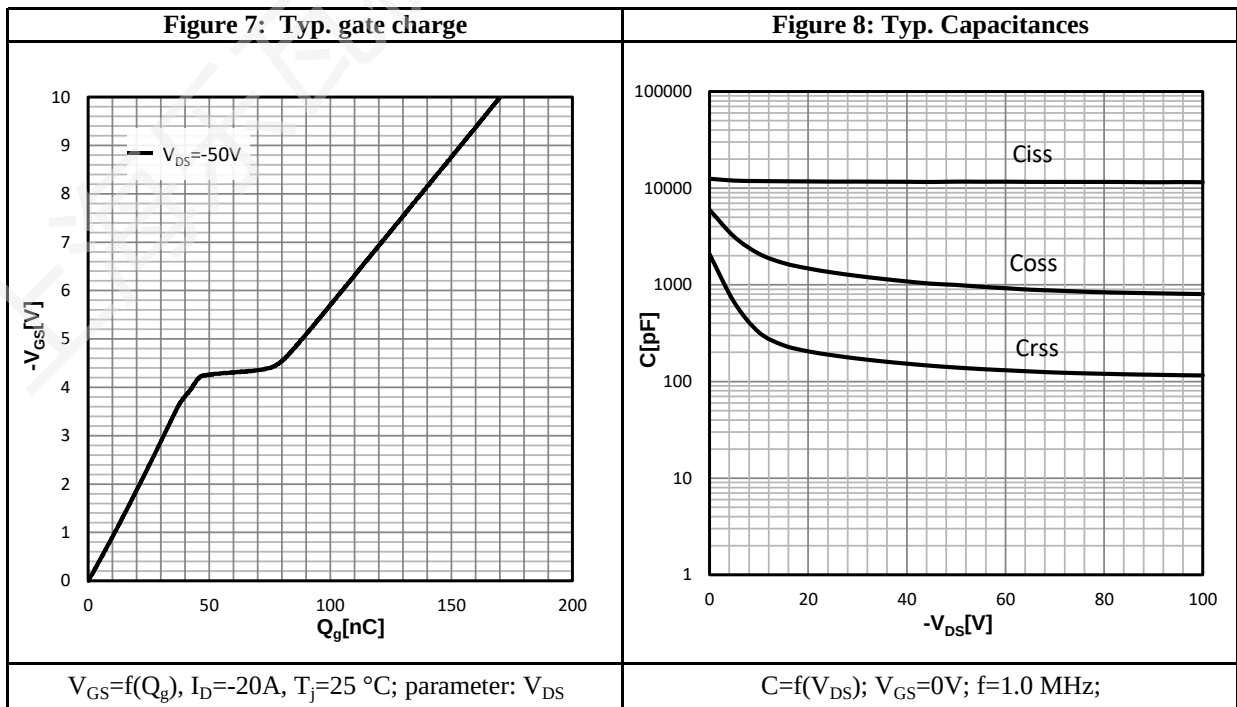
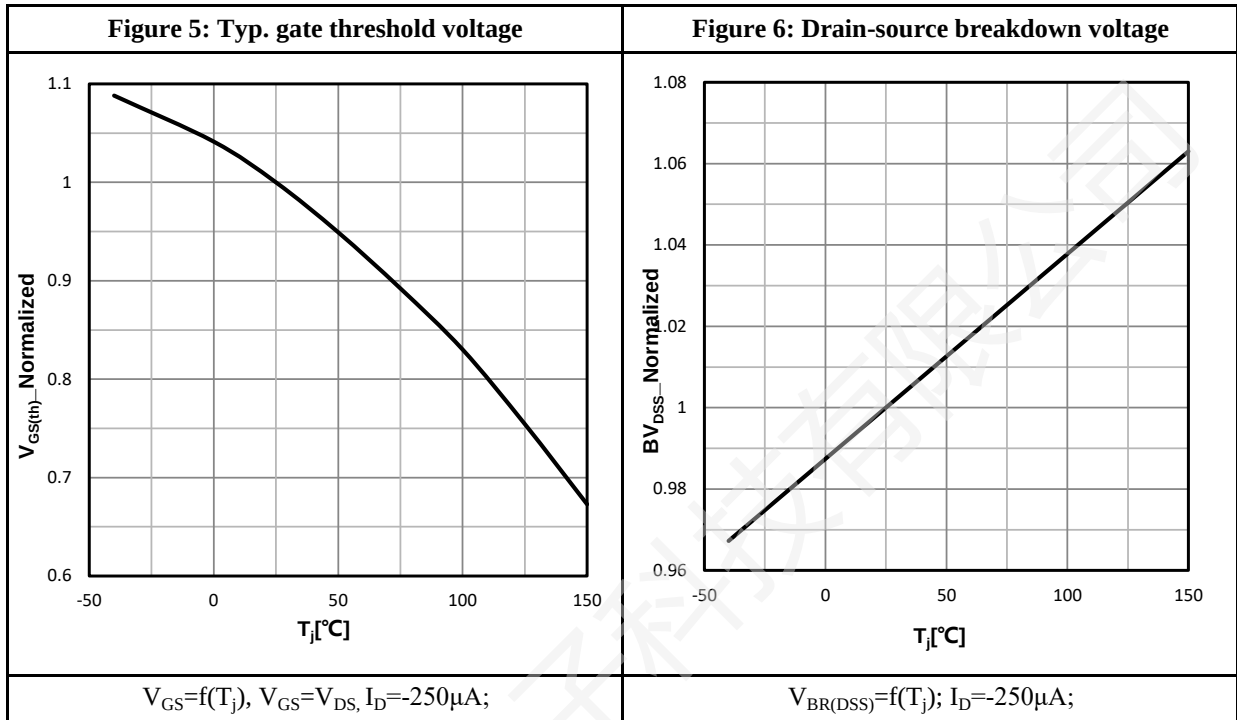
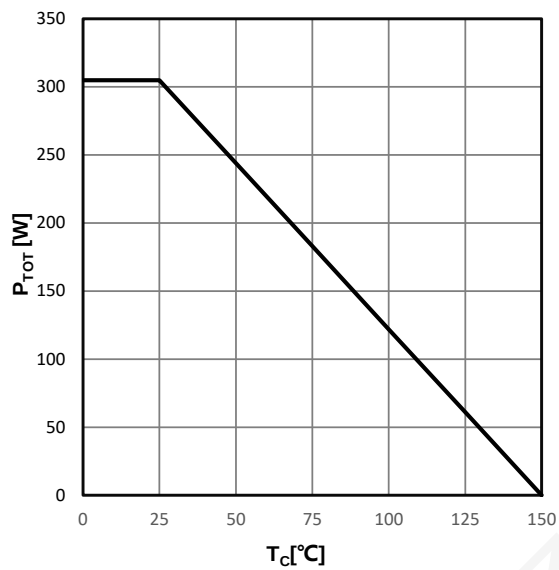
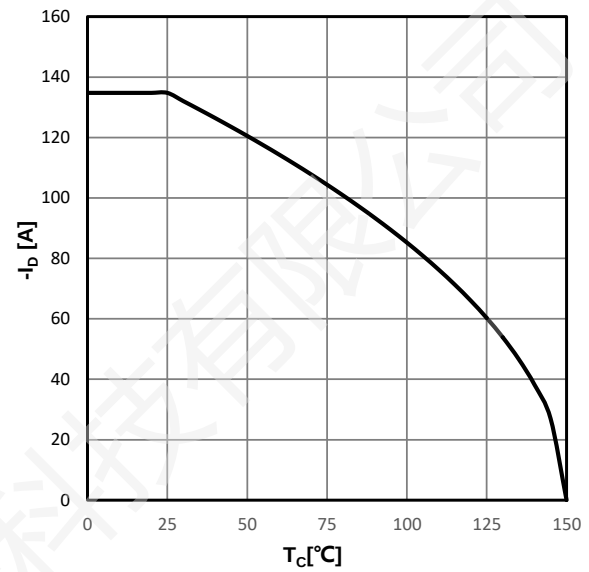
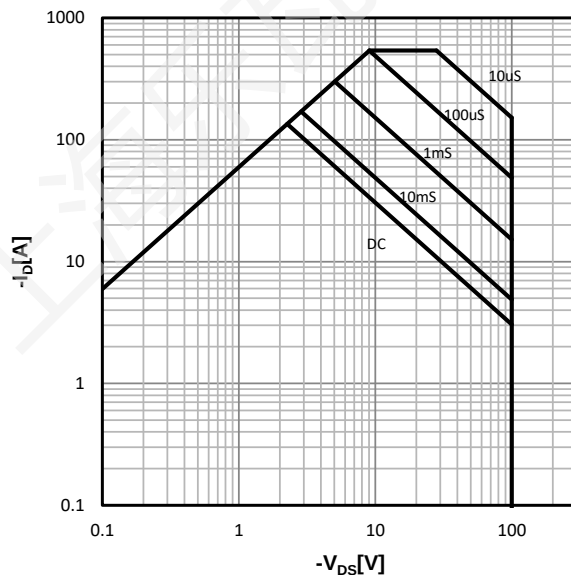


Figure 9: Power dissipation


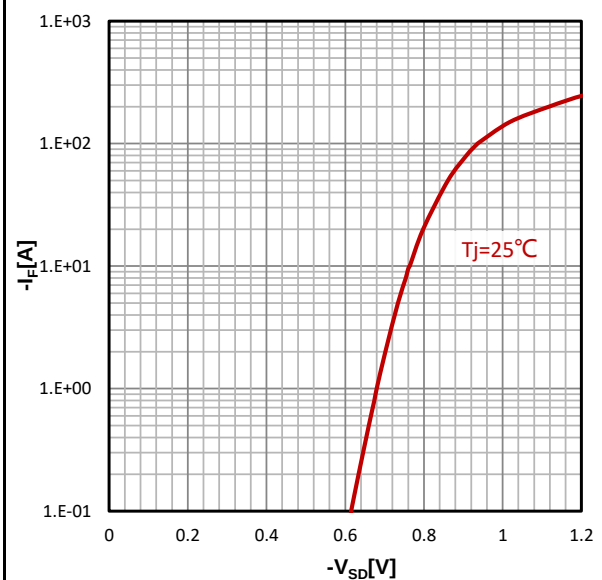
$$P_{tot}=f(T_C);$$

Figure 10: Drain current


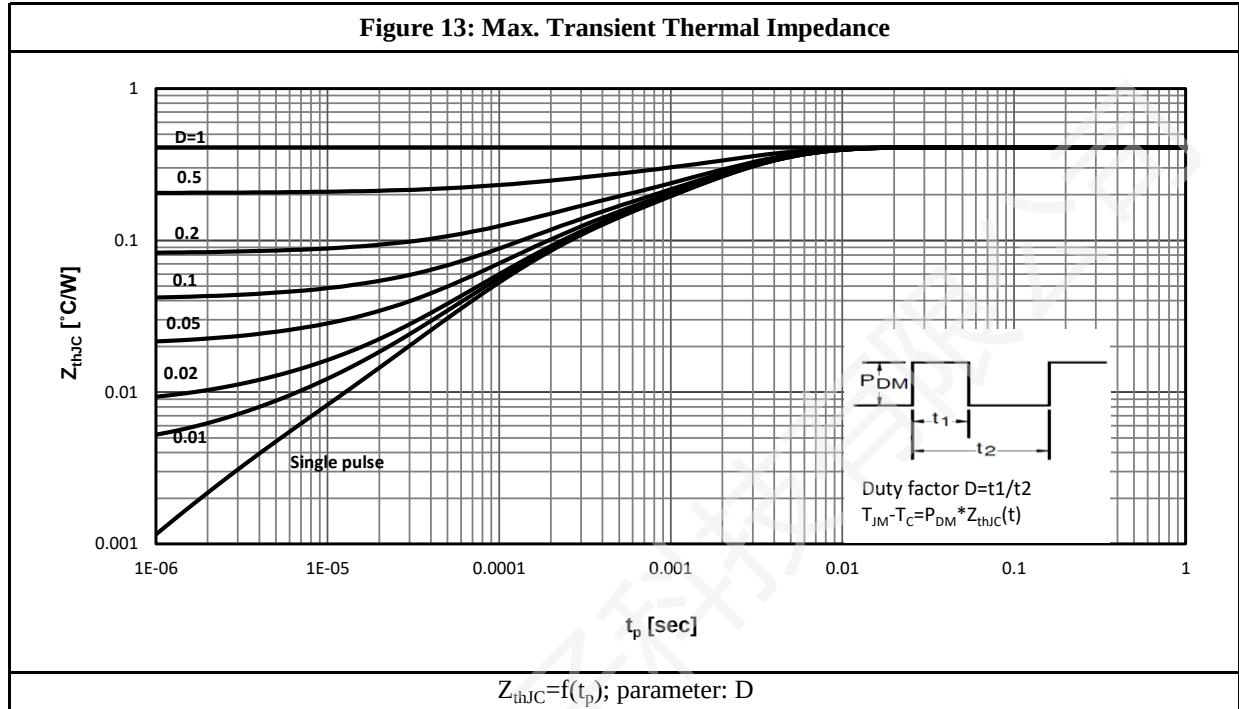
$$I_D=f(T_C);$$

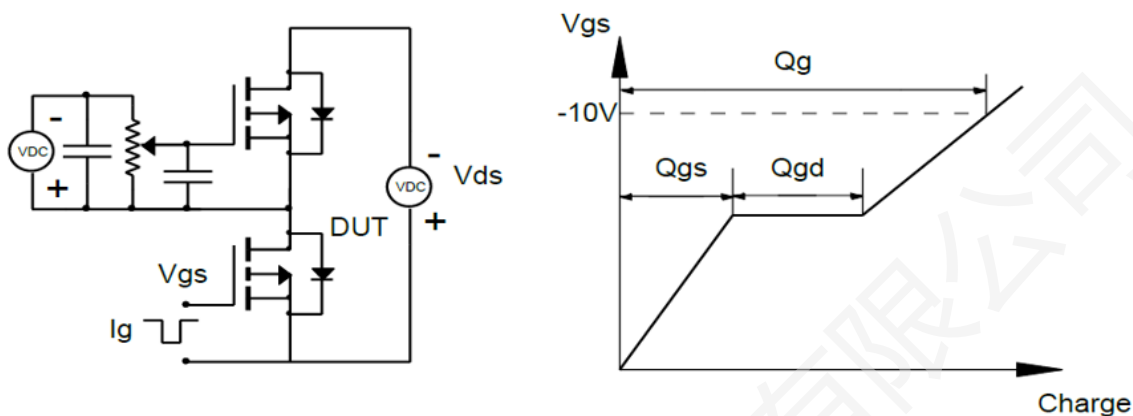
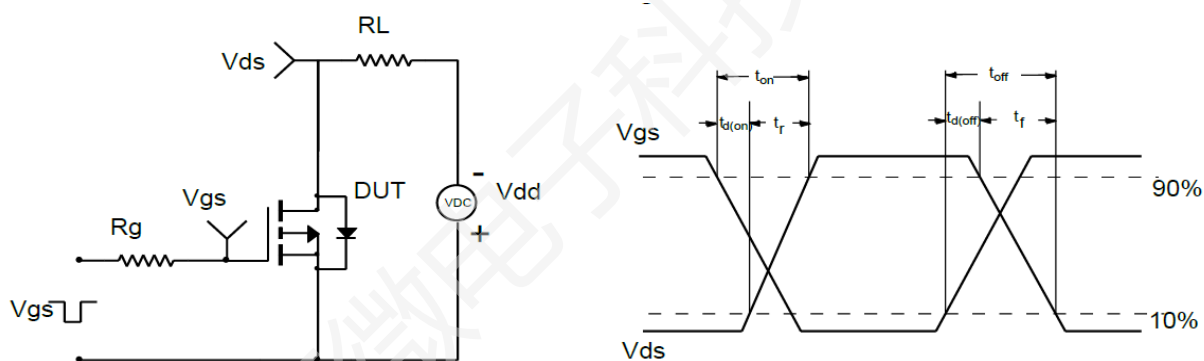
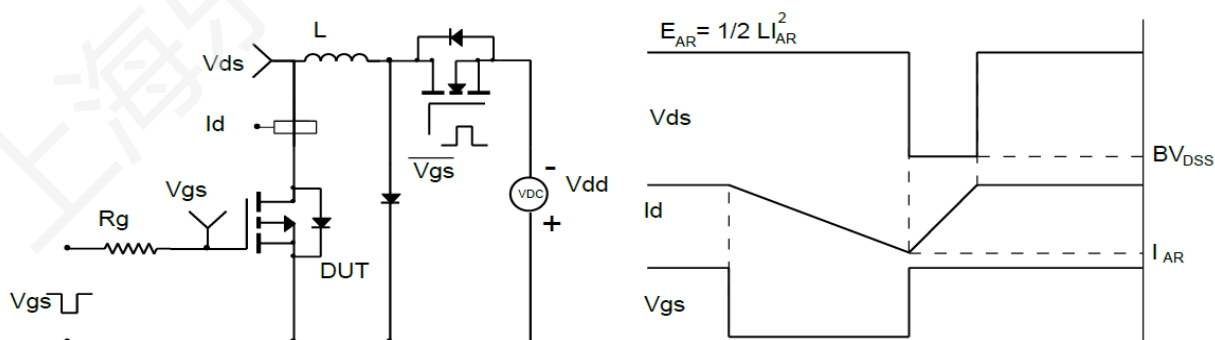
Figure 11: Safe operating area


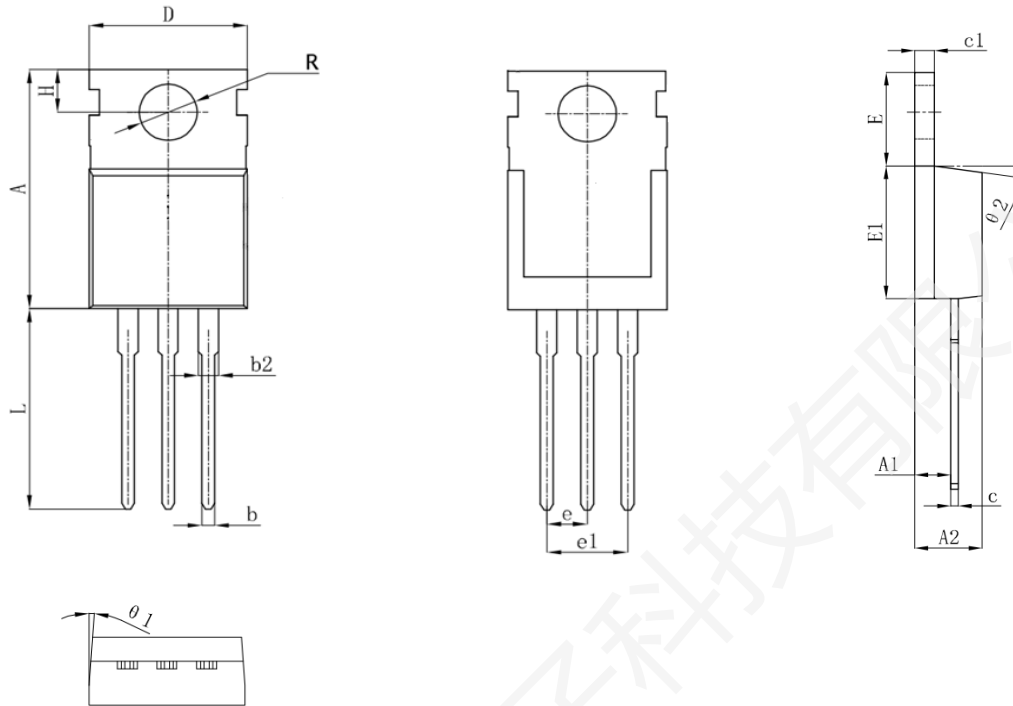
$$I_D=f(V_{DS}); T_C=25\text{ }^{\circ}\text{C}; D=0; \text{parameter: tp}$$

Figure 12: Typ. forward characteristics


$$I_F=f(V_{SD});$$

Figure 13: Max. Transient Thermal Impedance


Test Circuit & Waveform:

Figure 14: Gate Charge Test Circuit & Waveform

Figure 15: Resistive Switching Test Circuit & Waveforms

Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:


SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	15.3	15.55	15.8
A1	2.3	2.4	2.5
A2	4.4	4.5	4.7
b	0.7	0.8	0.9
b2	1.18	1.31	1.44
c	0.44	0.5	0.56
c1	1.28	1.3	1.33
D	9.8	10	12.2
E	6.4	6.5	6.6
E1	8.9	9.05	9.2
e	2.42	2.54	2.66
e1	4.84	5.08	5.32
H	2.73	2.8	2.87
H1	2.4	2.5	2.6
L	13.02	13.42	13.82
R	3.5	3.6	3.63
θ1	2°	2.5°	3°
θ2	6.5°	7°	7.5°

Revision History:

Revision	Date	Descriptions
Rev 1.0	Dec, 2025	Initial Version

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